

ABSTRACT OF THE DISCLOSURE

A mask pattern for multiple exposure for forming a resist pattern with an unvarying pattern pitch on a semiconductor wafer, which is
5 utilized as in case where a mask pattern under a design having the width of an aperture pattern smaller than the width of a light-shielding pattern is used at one exposure, wherein the mask pattern for multiple exposure has a pattern pitch that is the same as that of the mask
10 pattern under design and has the width of an aperture pattern greater than the width of a light-shielding pattern.